

Product features

High precision machining technology

Low temperature drift, high power.

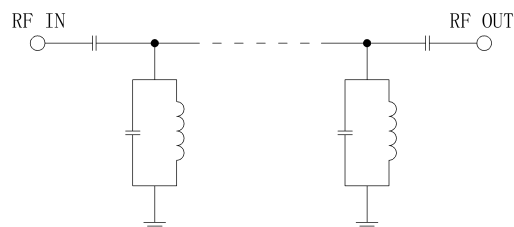
Ceramic substrate, 50 Ω coplanar waveguide

Gold wire bonding

参考图



Schematic diagram



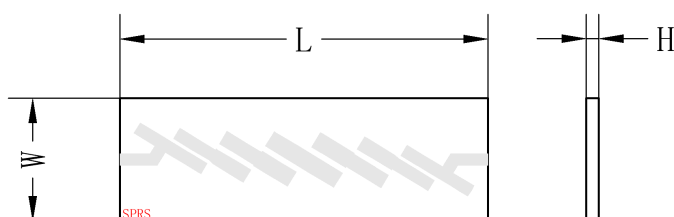
Tech specifications

Items	Parameters	Units
Center Frequency	39.6	GHz
Bandwidth	38.8-40.4	GHz
Center loss	2.5	dB
Ripple	1.0	dB
VSWR	1.7:1	
Group delay ripple	0.3	ns
Rejection	40@DC-37.1GHz	dBc
Rejection	40@42.4-50.0GHz	dBc

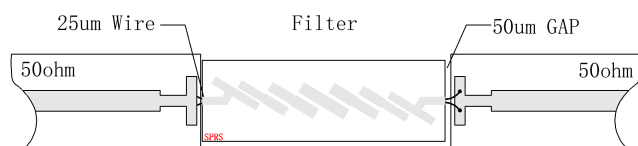
Other requirement (Design assurance)

power	2W CW
Operation Temp.	-55~+85°C
Storage Temp.	-55~+125°C
Outline size	L: 6.5, W: 2.0, h: 0.26

Outline drawing: Port centered



Suggested PCB Layout



PCB Rogers5880, h: 0.254mm	PCB Rogers4350B, h: 0.254mm
	

Note

- 1: The chip is recommended to be used in separate chambers, with one side 0.1mm away from the side wall and the surface 1.74mm away from the top cover. The ports are interchangeable;
- 2: Suggest using conductive adhesive for bonding;
- 3: The chip should be installed on materials such as Kovar (recommended) or copper with a thermal expansion coefficient similar to that of ceramics (6.7ppm/C), and the carrier thickness should be $\geq 0.2\text{mm}$;
- 4: Suggest using a T-shaped structure for microstrip bonding.
- 5: 由于加工精度误差个别产品会有调试胶补偿;

Typical test curve

